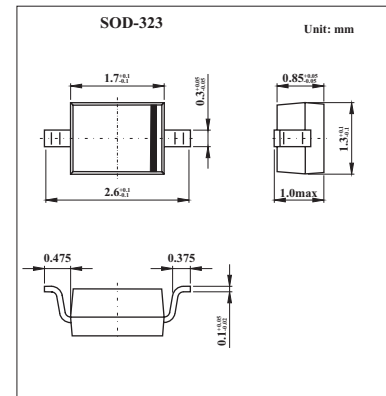


## Silicon Epitaxial Planar Diode

## 1SV324

## ■ Features

- High Capacitance Ratio:  $C_{1V}/C_{4V}=4.3$ (Typ.)
- Low Series Resistance:  $r_s=0.4\ \Omega$  (Typ.)
- Useful for Small Size Tuner

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

| Parameter                 | Symbol    | Value       | Unit             |
|---------------------------|-----------|-------------|------------------|
| Reverse Voltage           | $V_R$     | 10          | V                |
| Junction Temperature      | $T_j$     | 125         | $^\circ\text{C}$ |
| Storage Temperature Range | $T_{stg}$ | -55 to +125 | $^\circ\text{C}$ |

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

| Parameter         | Symbol          | Conditions                               | Min | Typ | Max  | Unit     |
|-------------------|-----------------|--|-----|-----|------|----------|
| Reverse Voltage   | $V_R$           | $I_R = 1\ \mu\text{A}$                   | 10  |     |      | V        |
| Reverse Current   | $I_R$           | $V_R = 10\ \text{V}$                     |     |     | 3    | nA       |
| Capacitance       | $C_{1V}$        | $f = 1\ \text{MHz}; V_R = 1\ \text{V}$   | 44  |     | 49.5 | pF       |
|                   | $C_{4V}$        | $f = 1\ \text{MHz}; V_R = 4\ \text{V}$   | 9.2 |     | 12   |          |
| Capacitance Ratio | $C_{1V}/C_{4V}$ |  | 4   | 4.3 |      |          |
| Series Resistance | $r_s$           | $V_R = 4\ \text{V}, f = 470\ \text{MHz}$ |     | 0.4 | 0.8  | $\Omega$ |

Note

1.Signal level when capacitance is measured:  $V_{sig} = 500\text{mV}_{rms}$ 

## ■ Marking

|         |    |
|---------|----|
| Marking | V8 |
|---------|----|